

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-9 (Canceled).

Claim 10 (Currently Amended): A method for producing a silicon single crystal by the Czochralski method, comprising the steps of using a silicon seed crystal ~~according to claim 1~~ wherein oxygen concentration in the seed crystal is 15ppma (JEIDA) or less, bringing a tip end of the seed crystal into contact with a silicon melt to melt the tip end of the seed crystal, performing necking operation, and growing a silicon single crystal.

Claim 11 (Currently Amended): A method for producing a silicon single crystal by the Czochralski method, comprising the steps of using a silicon seed crystal ~~according to claim 3~~ which does not have a straight body, bringing a tip end of the seed crystal into contact with a silicon melt to melt the tip end of the seed crystal, performing necking operation, and growing a silicon single crystal.

Claim 12 (Currently Amended): A method for producing a silicon single crystal by the Czochralski method, comprising the steps of using a silicon seed crystal ~~according to claim 1~~ wherein oxygen concentration in the seed crystal is 15ppma (JEIDA) or, bringing a tip end of the seed crystal into contact with a silicon

melt to melt the tip end of the seed crystal, and growing a silicon single crystal without performing necking operation.

Claim 13 (Currently Amended): A method for producing a silicon single crystal by the Czochralski method, comprising the steps of using a silicon seed crystal ~~according to claim 3~~ which does not have a straight body, bringing a tip end of the seed crystal into contact with a silicon melt to melt the tip end of the seed crystal, and growing a silicon single crystal without performing necking operation.